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### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	RDS(ON) MAX	<b>I</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
-30V	45mΩ @ V <sub>GS</sub> = -10V	-4.3A
-30 V	65mΩ @ V <sub>GS</sub> = -4.5V	-3.3A

## **Description**

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

### **Features**

- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

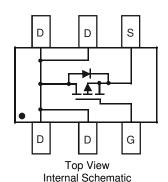
### **Mechanical Data**

- Case: SOT26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.016 grams (Approximate)

SOT26



Top View



### **Ordering Information** (Note 5)

Part Number	Qualification	Case	Packaging
DMP3056LDM-7	Commercial	SOT26	3000/Tape & Reel
DMP3056LDMQ-7	Automotive	SOT26	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



DMA = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)

M = Month (ex: 9 = September)

Date Code Key

Date Code Key												
Year	2008		~	2016		2017	2018		2019	2020	)	2021
Code	V		~	D		Е	F		G	Н		
								_				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code			_	4	Г		7	0	0		N.I.	



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	-30	V	
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$	I <sub>D</sub>	-4.3	Α
Continuous Diain Current (Note 7) VGS = 10V	t < 10s	$T_A = +25^{\circ}C$	ΙD	-5.8	Α
Maximum Continuous Body Diode Forward Curre	ent (Note 7)	Is	-2.3	Α	
Pulsed Drain Current (10μs Pulse, Duty Cycle =	1%)	I <sub>DM</sub>	-13	Α	

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	$P_{D}$	1.25	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	100	°C/W
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 7)  Steady State		$R_{ heta JA}$	86	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	15.6	C/VV
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

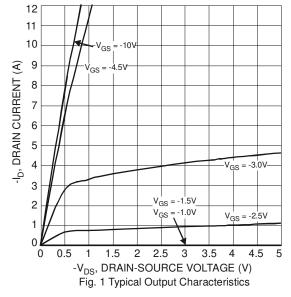
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

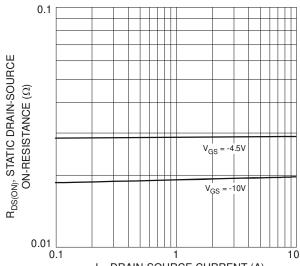
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS (Note 8)					•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V$ , $I_D = -250\mu A$	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{GS} = 0V, V_{DS} = -30V$	
Gate-Body Leakage Current	I <sub>GSS</sub>	_	_	±100 ±800	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 25V, V_{DS} = 0V$	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	_	-2.1	V	$V_{GS} = V_{DS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_		45 65	mΩ	$V_{GS} = -10V$ , $I_D = -5A$ $V_{GS} = -4.5V$ , $I_D = -4.2A$	
Forward Transconductance	<b>g</b> FS	_	8	_	S	$V_{DS} = -10V$ , $I_{D} = -4.3A$	
Diode Forward Voltage	$V_{SD}$	_	_	-1.2	V	$V_{GS} = 0V, I_S = -1.7A$	
DYNAMIC PARAMETERS (Note 9)							
Input Capacitance		_	948	_	рF	), o), ), os, )	
Output Capacitance		_	105	_	pF	$V_{GS} = 0V, V_{DS} = -25V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	100	_	pF	-1 = 1.0IVIH2	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Qg	_	10.1		nC	$V_{DS} = -15V$ , $V_{GS} = -4.5V$ , $I_{D} = -6A$	
	$Q_g$		21.1	_		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V.	
Gate-Source Charge		_	2.8	_	nC	VDS = -15V, VGS = -10V, In = -6A	
Gate-Drain Charge		_	3.2			ID = -6A	
Gate Resistance	$R_g$	_	13.15	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10.2	_			
Rise Time	t <sub>R</sub>	_	6.6	_		$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	50.1	_	ns	$I_D = -1A$ , $R_g = 6.0\Omega$	
Fall Time		_	22.3	_			

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







-I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

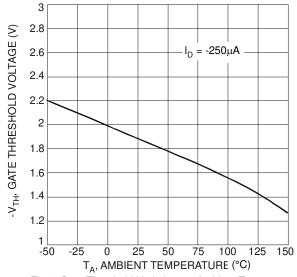
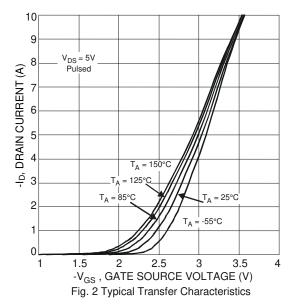


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



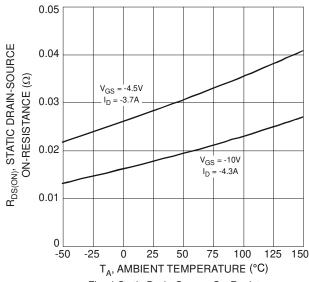


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

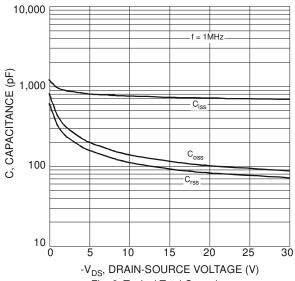


Fig. 6 Typical Total Capacitance



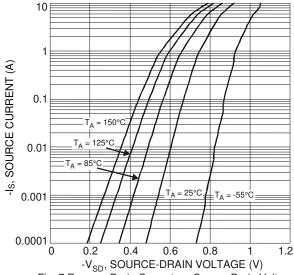
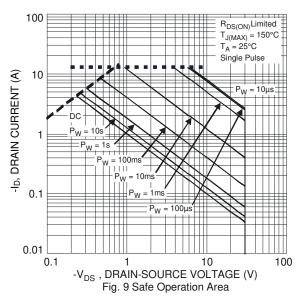


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



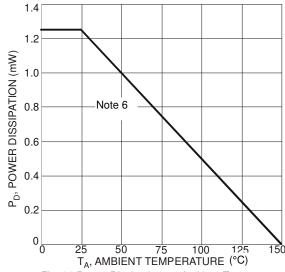


Fig. 11 Power Dissipation vs. Ambient Temperature

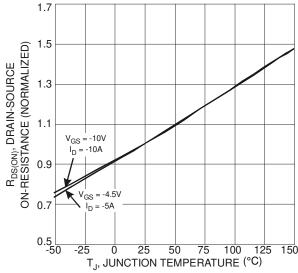
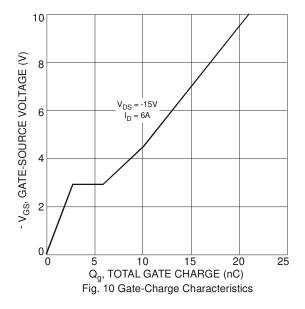
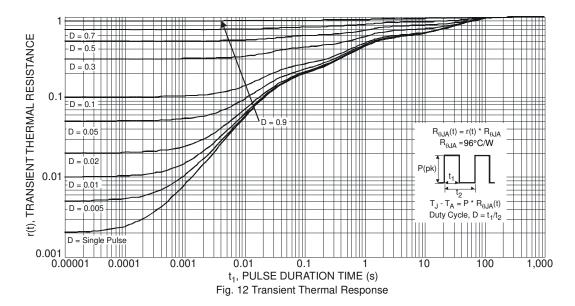


Fig. 8 On-Resistance Variation with Temperature



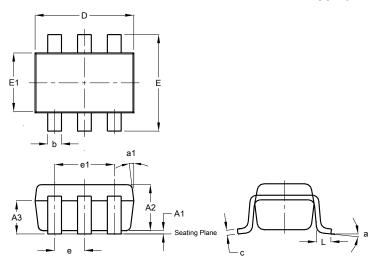




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT26

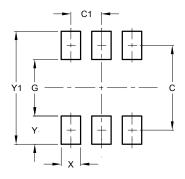


SO126								
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	1	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
X	0.55
Υ	0.80
Y1	3.20



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